Contents lists available at ScienceDirect



Computational and Theoretical Chemistry

journal homepage: www.elsevier.com/locate/comptc



The computational probing of carrier transport in $MAPbI_{3-x}Cl_x$

Kan Wang^{a,b}, Junxiang Xiang^{a,c}, Rai Nauman Ali^{a,c}, Bin Xiang^{a,c,*}, Xudong Cui^{a,b,*}

^a Photonic Technology Research and Development Center, Quanzhou Normal University, No 398, Donghai Main Street, Quanzhou, Fujian 362000, China

^b Sichuan New Materials Research Center, Institute of Chemical Materials, CAEP, Chengdu, Sichuan 610200, China

^c Department of Materials Science & Engineering, CAS Key Lab of Materials for Energy Conversion, Synergetic Innovation Center of Quantum Information & Quantum

Physics, University of Science and Technology of China, Hefei, Anhui 230026, China

ARTICLE INFO	A B S T R A C T
<i>Keywords:</i> MAPbI _{3-x} Cl _x perovskites DFT calculations Cl incorporation Carrier transport performance	MAPbI _{3-x} Cl _x (MA) perovskite has attracted much research attention because of its remarkable carrier transport performance. However, the influence of Cl incorporation in MAPbI _{3-x} Cl _x perovskite on the carrier transport performance still remains unclear. With the first-principles calculations, we found that with the incorporation of the small ionic radius of Cl ⁻ , it forces the orientation of MA molecule turning from diagonal direction to axial direction. As a result, this induced lattice polarization enhances the carrier transport along the axial direction. In the light doping direction, we confirmed that the carrier transports for both electrons and holes are suppressed due to a large lattice scattering. However, in the heavy doping direction, we found that the decrease of carrier mobility is mainly caused by the energy states up-shift because of the Pb position deviation for electrons and the strong localization of Cl 3p states for holes.

1. Introduction

Solar cell device performance has a large dependency on the optical absorption and the carrier transport of the involved photovoltaic materials. Organic-inorganic perovskites materials (ABX₃, A = organic molecule, B = metal, X = halide) are one type of promising solar cell materials because of their outstanding optical and electronic properties with the low-cost synthetic methods [1–3]. The tunable band-gaps make the optical absorption spectrum almost over the entire visible range and the long balanced carrier diffusion length larger than 100 nm in solution-processed pure iodide perovskites also shows their great capability of carrier transport [4]. Therefore, high photoelectric conversion efficiencies of 20.1% for perovskites are recently achieved [5], indicating the great potential in thin-film solar cell application for organic-inorganic perovskites materials.

Besides the rapid developments of MAPbI₃ perovskites, it is also reported that their optical and electronic properties can be further optimized by introducing other halide ions like CI^- and Br^- into the perovskite materials. Stranks et al. have first reported that the electronhole diffusion lengths could have a tenfold increase by introducing $CI^$ ions into MAPbI₃ perovskites, indicating better carrier transport [6]. Wehrenfenning et al. have also confirmed the improved carrier mobility in mixed halide perovskites by using transient THz spectroscopy [7]. Furthermore, it has been obtained the improved carrier mobility and the reduced carrier recombination rates for $MAPbI_{3-x}Br_x$ and $MABr_{3-x}Cl_x$ [8,9].

However, the research about mixed halide MAPbI_{3-x}Cl_x perovskite is still under debate since the existence and effects of the incorporated chlorine is questionable and unclear. Scientists were confused about the exact role of the doping chloride for the enhanced carrier transport performance. Some researchers believed that the incorporated Cl has a direct influence to the enhanced carrier transport. For example, Wehrenfenning et al. suggested that the incorporated Cl would change the electronic structure of perovskite to reduce the spatial overlap of the electron and holes [7]. Therefore, the bimolecular recombination rates can be decreased for the long carrier diffusion length. Colella et al. also proposed that the Cl in the MAPbI₃ perovskite can act as a dopant to improve the transport properties [10]. However, other researchers suggested that the incorporated Cl would make an indirect influence like the suppression of impurities and defects. Du reported that the incorporated Cl can suppress the formation of interstitial I defect which is calculated to be a deep level defect [11]. It implied that the high carrier transport performance is an instinct character of MAPbI3 perovskite, and the incorporated Cl is just helpful to remove the carrier recombination center in the perovskites. Furthermore, some reports pointed out that the Cl has little or even none contribution to the enhanced carrier transport since the Cl is hard to incorporate into MAPbI₃ perovskite [10]. Only a very low concentration (below 3-4%) of

* Corresponding authors at: Photonic Technology Research and Development Center, Quanzhou Normal University, No 398, Donghai Main Street, Quanzhou, Fujian 362000, China (R.N. Ali).

E-mail addresses: binxiang@ustc.edu.cn (B. Xiang), xudcui@caep.cn (X. Cui).

https://doi.org/10.1016/j.comptc.2018.06.012 Received 22 May 2018; Received in revised form 14 June 2018; Accepted 14 June 2018 Available online 18 June 2018

2210-271X/ $\ensuremath{\mathbb{C}}$ 2018 Published by Elsevier B.V.

chloride can be incorporated into an iodide-based structure, in accordance with DFT calculations that the formation energy of MAP- $bI_{3-x}Cl_x$ (MA) is much higher than MAPbI₃ perovskite [12].

The mechanism for the enhanced carrier transport in MAPbI₃ perovskite still remains challenging. Therefore, we have systematically studied the influence of incorporated Cl on the carrier transport property of MAPbI₃ perovskite by using the first-principles calculations. We found that the Cl incorporation was not able to directly improve the carrier transport performance, but cause a large decrease for carrier mobility due to the energy state up-shift and the lattice scattering. We suggest that the observed high carrier transport performance of MAPbI_{3-x}Cl_x perovskites in reported experiments could be attributed to the suppression of the disorder orientation of polar molecule MA caused by the Cl incorporation.

2. Methods

The geometry optimization and electronic calculations for MAPbI₃, MAPbI₂Cl, MAPbI_{2.5}Cl_{0.5} and MAPbI_{2.667}C_{0.333} perovskites are performed using the VASP code in the framework of DFT [13,14]. The PAW pseudo-potential is used with a cut-off energy of 500 eV for the plane-wave basis functions [15]. This computational approach has been carefully tested to guarantee its validity (detailed results are listed in Table S1.). For Cl doping concentration calculations, a cubic MAPbI₃ unit cell, $2 \times 1 \times 1$ and $3 \times 1 \times 1$ supercells are built with one Cl replacing with one I atom in the x axis, corresponding to a doping concentration of 33.3%, 16.7 and 11.1%, respectively. The $8 \times 8 \times 8$ Monkhorst-pack k-meshes is employed for structure optimization of MAPbI₃, MAPbI₂Cl and $4 \times 8 \times 8$, $3 \times 8 \times 8$ Monkhorst-pack k-meshes for MAPbI_{2.5}Cl_{0.5} and MAPbI_{2.667}C_{0.333} perovskites, respectively. The lattice vectors and atomic positions are relaxed until the total energy changed by less than 1×10^{-5} eV. The carrier mobility is calculated based on the deformation potential theory as shown below [16]:

$$\mu = \frac{8\pi^{1/2}\hbar^4 ec_{ii}}{3(m^*)^{5/2}(k_BT)^{3/2}E_1^2}$$

where \hbar is the reduced Planck constant, e is the element charge, c_{ii} is the elastic constant, m^* is the effective mass of charge, k_B is the Boltzmann constant, T is the absolute temperature, and E_1 is the deformation potential defined as the energy shift of the band energy position (ΔE) with respect to a small lattice dilation (Δl) along a lattice (l_0) direction, i.e., $E_1 = \Delta E/(\Delta l/l_0)$ [17,18]. Room temperature (T = 300 K) is used in our calculation.

3. Results and Discussion

We firstly considered the situation that one Cl atom is incorporated into one cubic phase MAPbI₃ perovskite unit cell, which corresponds to a high doping concentration of 33.3%. The optimized lattice structure of MAPbI₃ and MAPbI₂Cl were shown in Fig. 1. The calculated lattice parameters were a = b = c = 6.47 Å for MAPbI₃, consistent with previous report [19]; a = 5.78 Å, b = c = 6.53 Å for the MAPbI₂Cl perovskite. Due to the small ionic radius of Cl⁻, the lattice parameter along *x* axis is largely shortened, and the orientation of MA molecule has turned from $\langle 1 \ 1 \ \rangle$ to nearly $\langle 0 \ 1 \ \rangle$ direction because of this spatial compression. Meantime, it can also be found that the deviation of the Pb atom from the lattice central become larger in MAPbI₂Cl perovskites with a Cl–Pb–Cl bond angle of 168.0°, much smaller than the average I–Pb–I bond angle of 176.2° along each axis in MAPbI₃ perovskites (Fig. 1).

The carrier transport performance for MAPbI₃ and MAPbI₂Cl perovskites were evaluated based on the deformation potential theory with effective mass approximation as shown in Table 1. The calculated carrier mobility of MAPbI₃ perovskite is up to ~16,889 cm²V⁻¹s⁻¹ for electrons and 966 cm²V⁻¹s⁻¹ for holes, respectively, consistent with other theoretical work [20,21]. Such high carrier mobility can be attributed to the small effective mass for electrons and holes. However, after the Cl is incorporated into the perovskite structure, there is a huge decrease in the carrier mobility for both electrons and holes along the $\langle 1\ 0\ 0\rangle$ direction (the Cl doping direction) because of the large carrier effective mass for electrons of 0.86 m_0 and holes of 0.47 m_0. Especially, the holes have a better carrier transport performance than electrons, opposite to that in the original MAPbI₃ perovskite. Meanwhile, along the $\langle 0\ 1\ 0\rangle$ direction which is less influenced by the Cl doping, it is surprised to see that both the electrons and holes experience an increase in carrier mobility, even larger than that in the original MAPbI₃ perovskite. It is attributed to the smaller effective mass of 0.07 m_0 for electrons and 0.17 m_0 for holes. It implies that the carriers transport in the MAPbI₂Cl perovskite is largely suppressed in the doping direction, but can also be enhanced in other two directions.

In order to understand the underlying mechanisms for these carrier mobility changes, we carried out the band structure and density of states calculations for MAPbI₃ and MAPbI₂Cl perovskites as shown in Fig. 2. Both of these two perovskites are direct band-gap semiconductors with the band-gap of 1.57 and 1.78 eV at the R-point, respectively. In MAPbI₃ and MAPbI₂Cl perovskites, the conduction band minimum (CBM) is mainly occupied by Pb 6p states and the valence band maximum (VBM) is mainly occupied by I 5p states. No impurity energy bands were found in the band-gap for the Cl incorporation since the energy of Cl 3p states are smaller than the energy of I 5p states, and these energy bands merge into the middle of the VBM.

The decrease in hole mobility along the <100> direction in MAPbI₂Cl can be easily understood since the Cl 3p states have a smaller energy than I 5p. Therefore, the localization for the carriers can be much strong around the Cl, resulting in a large hole effective mass of 0.47 m₀ along $\langle 1 0 0 \rangle$ direction. For the electron mobility, the CBM is nearly three-fold degenerated in the MAPbI₃ perovskite, corresponding to the energy states in Pb $6p_x$, $6p_y$ and $6p_z$ orbits. As a result, we can find that the electrons along the $\langle 1 0 0 \rangle$ direction of MAPbI₃ perovskite have a light effective mass of 0.09 m₀ and two heavy effective masses of 0.42 m₀ and 0.74 m₀, respectively. In the MAPbI₂Cl perovskite, the CBM is only two-fold degenerated, while the third energy state moves up with an energy split of 0.47 eV. Due to this energy state up-shift, only two heavy effective masses for electrons $(0.86 m_0 \text{ and } 1.09 m_0)$ were left behind along the R - Q path, leading to a small electron mobility in the $\langle 1 0 0 \rangle$ direction. Based on the electron density distribution calculations shown in Fig. 3, we found that the energy state split can be attributed to the strong Pb 6p_x – Cl 3p_y anti-bonding orbital interaction (Fig. 3b). It was caused by the large deviation of Pb position in the <010> direction, leading to the energy level raising of the CBM state of Pb 6px character; while the CBM states of Pb 6pv and 6pz character almost remain the same since they only have a little antibonding interaction with I $5p_x$ and $5p_z$ orbits (Fig. 3a).

Although there is a large decrease in carrier mobility along the <100> direction due to the Cl incorporation, the MAPbI_2Cl perovskite exhibits an enhanced carrier transport performance in the <010> direction with a carrier mobility of 24,474 cm²V⁻¹s⁻¹ for electrons and 1467 cm²V⁻¹s⁻¹ for holes, respectively. As there is no Cl involved in the <010> direction, we believe this enhanced carrier mobility can be attributed to the re-orientated polar molecule MA. Since the MA is orientated from <111> to nearly <011> direction, the lattice polarization of MAPbI_2Cl perovskite along <010> direction increases, leading to a smaller carrier effective mass of 0.07 m₀ for electrons and 0.18 m₀ for holes. Therefore, it enhances the carrier mobility.

To further confirm the MA molecule orientation contribution in the carrier transport performance, we also calculated the electronic properties of the MAPbI₃ perovskite with the MA orientation fixed in $\langle 1 \ 0 \ 0 \rangle$ direction as shown in Fig. 4. The calculated band gap is 1.67 eV, larger than the band gap of 1.57 eV in the MAPbI₃ with the MA orientated in $\langle 1 \ 1 \ 1 \rangle$ direction. It originates from the up-shift of the CBM once the polarization direction of MA is changed. The calculated carrier effective mass is 0.70 m₀ and 0.20 m₀ in $\langle 1 \ 0 \ 0 \rangle$ direction for

Download English Version:

https://daneshyari.com/en/article/7838783

Download Persian Version:

https://daneshyari.com/article/7838783

Daneshyari.com